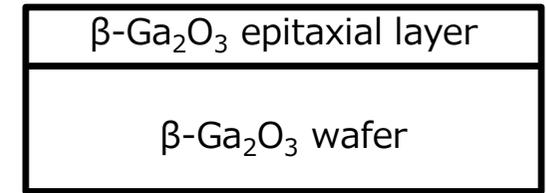


Standard specifications of 10×15 mm² β-Ga₂O₃ epitaxial wafer (by MBE)

Epitaxial layer

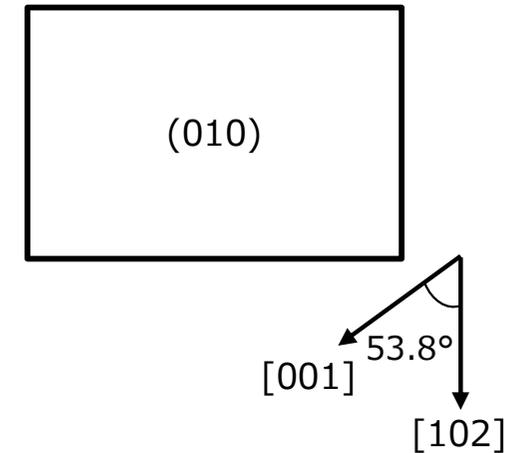
Items	Specifications	
Dopant	Si (n-type)	Undoped (semi-insulating)
Doping concentration <small>*A value can be selected within the described range.</small>	Specify a value in the range between 1×10^{17} and $2 \times 10^{18} \text{ cm}^{-3}$	-
Thickness <small>*A value can be selected within the described range.</small>	Specify a value in the range between 0.1 and 0.5 μm	



Cross section of β-Ga₂O₃ epitaxial wafer

Wafer

Items	Specifications	
Dopant	Sn (n-type)	Fe (semi-insulating)
Doping concentration	Using the range of $1 \sim 9 \times 10^{18} \text{ cm}^{-3}$	-
Resistivity	-	$\geq 10^{10} \Omega\text{cm}$
Orientation	(010)	
Size	10×15 mm ²	
Thickness	0.5 mm	
XRD FWHM	$\leq 150 \text{ arcsec}$	
Off set angle	$0^\circ \pm 1^\circ$	



Orientation



Remarks

- 1 These products must be used for research and development purposes only.
- 2 The substrates must not be used as a seed crystal.
- 3 The specifications are subject to change without notice.